

DESCRIPTION

2SC3247 is a silicon NPN epitaxial type transistor. Designed with high voltage, high collector current, dissipation and high h_{FE} .

Complementary with 2SA1287.

FEATURE

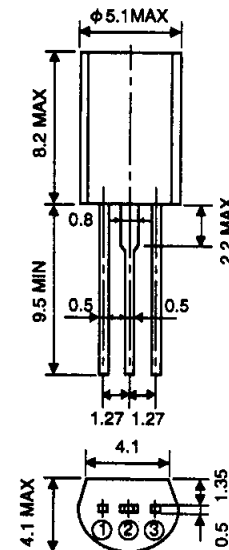
- High h_{FE} $h_{FE}=600$ to 1800
- High voltage $V_{CEO}=50V$
- Low collector to emitter saturation voltage
 $V_{CE(sat)}=0.15V$ ($I_C=500mA$, $I_B=10mA$)
- High collector dissipation $P_C=900mW$

APPLICATION

Relay drive or power supply for audio machine, VCR, and other electronic machine.

OUTLINE DRAWING

Unit:mm

**TERMINAL CONNECTOR**

- ① : EMITTER
② : COLLECTOR EIAJ : —
③ : BASE JEDEC : —

Note)

The dimension without tolerance represent central value.

MAXIMUM RATINGS ($T_a=25^\circ C$)

Symbol	Parameter	Ratings	Unit
V_{CBO}	Collector to Base voltage	50	V
V_{EBO}	Emitter to Base voltage	6	V
V_{CEO}	Collector to Emitter voltage	50	V
I_{CM}	Peak collector current	2	A
I_C	Collector current	1	A
P_C	Collector dissipation($T_a=25^\circ C$)	900	mW
T_j	Junction temperature	+150	$^\circ C$
T_{stg}	Storage temperature	-55 to +150	$^\circ C$

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ C$)

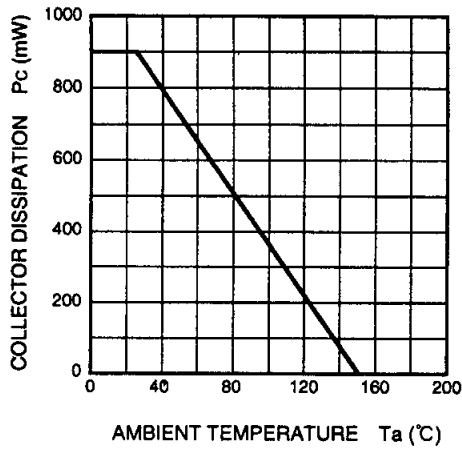
Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
$V_{(BR)CBO}$	C to B break down voltage	$I_C=10\mu A, I_E=0$	50			V
$V_{(BR)EBO}$	E to B break down voltage	$I_E=10\mu A, I_C=0$	6			V
$V_{(BR)CEO}$	C to E break down voltage	$I_C=1mA, R_{BE}=\infty$	50			V
I_{CBO}	Collector cut off current	$V_{CB}=40V, I_E=0$			0.1	μA
I_{EBO}	Emitter cut off current	$V_{EB}=2V, I_C=0$			0.1	μA
h_{FE}^*	DC forward current gain	$V_{CE}=6V, I_C=100mA$	600		1800	—
$V_{CE(sat)}$	C to E saturation voltage	$I_C=500mA, I_B=10mA$		0.15	0.5	V
f_T	Gain band width product	$V_{CE}=10V, I_E=-10mA$		130		MHz
C_{ob}	Collector output capacitance	$V_{CB}=10V, I_E=0, f=1MHz$		12		pF

* It shows h_{FE} classification in right table.

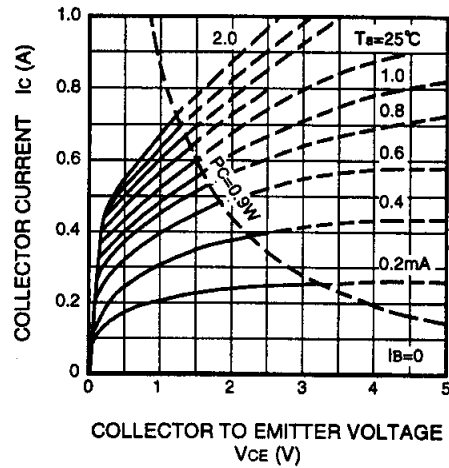
Item	H	J
h_{FE}	600 to 1200	900 to 1800

TYPICAL CHARACTERISTICS

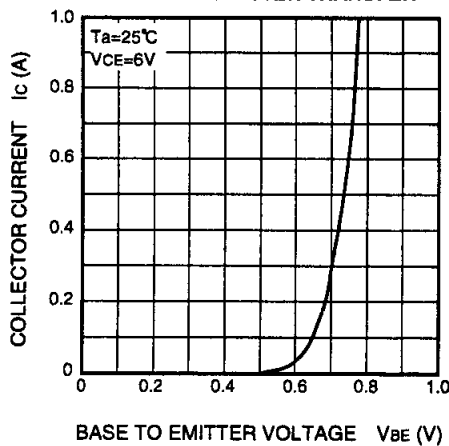
**COLLECTOR DISSIPATION VS.
AMBIENT TEMPERATURE**



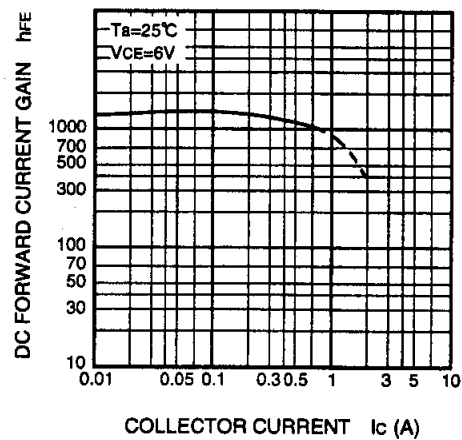
COMMON EMITTER OUTPUT



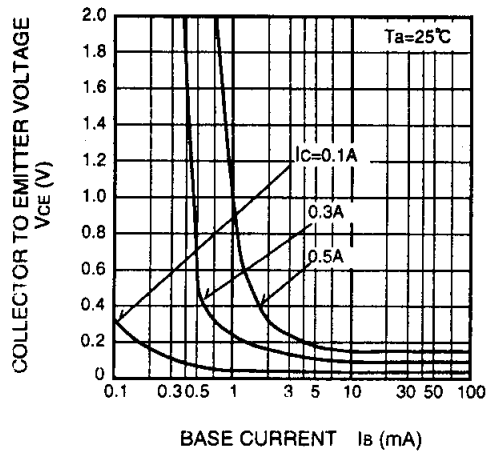
COMMON EMITTER TRANSFER



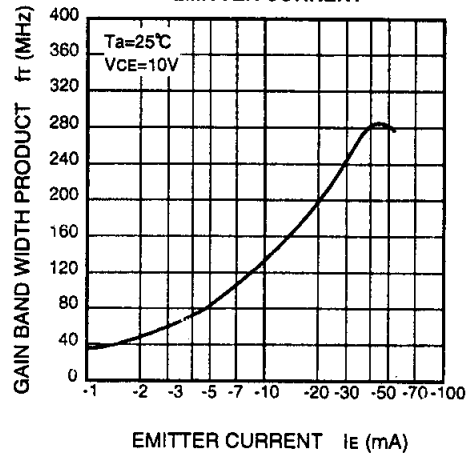
**DC FORWARD CURRENT GAIN
VS. COLLECTOR CURRENT**



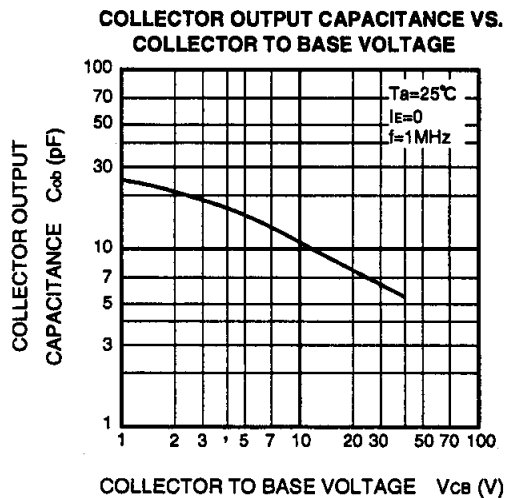
**COLLECTOR TO EMITTER SATURATION
VOLTAGE VS. BASE CURRENT**



**GAIN BAND WIDTH PRODUCT VS.
EMITTER CURRENT**



FOR RELAY DRIVE, POWER SUPPLY APPLICATION
SILICON NPN EPITAXIAL TYPE





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